

REMARKS

Reconsideration and allowance of this application, as amended, are respectfully requested.

Claims 9-12 stand rejected under 35 USC 102(b) as being anticipated by Chen et al (US Patent No. 5,545,574). Applicant respectfully traverses the rejection.

Claims 9 and 10 are cancelled by this amendment. Claim 11 is amended as to form and to emphasize more clearly some patentable differences over the references of record.

Amended claim 11 recites a method of manufacturing a semiconductor device that includes, among other things, depositing a film which inhibits silicidation on the source-drain diffusion layer by a CVD method. Chen does not teach or suggest the use of a CVD process for the production of a silicidation inhibiting layer.


In contrast, Chen et al. merely teaches the use of a diffusion-type thermal process. Specifically, Chen states: "The exposed surface 42, 41 and 46 are introduced to a nitrogen-containing material to form regions 52, 54 and 56." The Office Action acknowledges that Chen does not discuss selective deposition of the silicidation-inhibiting layer and in fact it is evident that there is no deposition, selective or otherwise, at all discussed in Chen for this purpose. The reference merely describes forming regions 52, 54 and 56 by a thermal reaction using an ambient environment including ammonia, nitric oxide, nitrous oxide, nitrogen or the like (see column 3, lines 38-40) but does not suggest anything regarding deposition of material to form the regions 52, 54 and 56. Thus, Chen et al. fails to teach or suggest the subject matter recited in amended claim 11 including at least: "***depositing*** a film which inhibits silicidation on the source-drain diffusion layer ***by a CVD method***".

Claim 12 depends from and further limits claim 11 and thus, should also be patentable. All other claims are either cancelled or withdrawn from consideration.

All matters having been addressed, a Notice of Allowance for the claims, as amended,
is solicited.

Respectfully submitted,

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